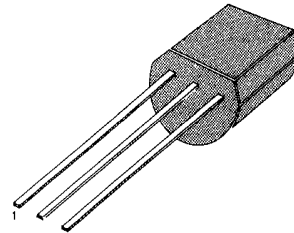


SS9011**NPN EPITAXIAL SILICON TRANSISTOR****AM CONVERTER, AM/FM IF AMPLIFIER
GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	30	mA
Collector Dissipation	P _C	400	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ 150	°C

TO-92



1. Emitter 2. Base 3. Collector

ELECTRICAL CHARACTERISTICS (T_A=25 °C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = 100 μA, I _E = 0	50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 1 mA, I _B = 0	30			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 100 μA, I _C = 0	5			V
Collector Cut-off Current	I _{CBO}	V _{CB} = 50 V, I _E = 0			100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5 V, I _C = 0			100	nA
DC Current Gain	h _{FE}	V _{CE} = 5 V, I _C = 1 mA	28	90	198	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 10 mA, I _B = 1 mA		0.08	0.3	V
Base-Emitter Voltage	V _{BE}	V _{CE} = 5 V, I _C = 1 mA	0.65	0.7	0.75	V
Output Capacitance	C _{OB}	V _{CB} = 10 V, I _E = 0 f = 1 MHz		1.5		pF
Current Gain-Bandwidth Product	f _T	V _{CE} = 5 V, I _C = 1 mA	150	370		MHz
Noise Figure	NF	V _{CE} = 5 V, I _C = 1.0 mA f = 1 MHz, R _S = 500 Ω		2.0	4.0	dB

h_{FE} CLASSIFICATION

Classification	D	E	F	G	H	I
h _{FE}	28-45	39-60	54-80	72-108	97-146	132-198

